Product Preview

Complementary ThermalTrakTM Transistors

The ThermalTrak family of devices has been designed to eliminate thermal equilibrium lag time and bias trimming in audio amplifier applications. They can also be used in other applications as transistor die protection devices.

Features

- Thermally Matched Bias Diode
- Instant Thermal Bias Tracking
- Absolute Thermal Integrity
- High Safe Operating Area

Benefits

- Eliminates Thermal Equilibrium Lag Time and Bias Trimming
- Superior Sound Quality Through Improved Dynamic Temperature Response
- Significantly Improved Bias Stability
- Simplified Assembly
 - Reduced Labor Costs
 - Reduced Component Count
- High Reliability

Applications

- High-End Consumer Audio Products
 - Home Amplifiers
 - Home Receivers
- Professional Audio Amplifiers
 - Theater and Stadium Sound Systems
 - ◆ Public Address Systems (PAs)



ON Semiconductor®

http://onsemi.com

BIPOLAR POWER TRANSISTORS 15 A, 230 V, 200 W



TO-264, 5 LEAD CASE 340AA STYLE 1

MARKING DIAGRAM

SCHEMATIC





xxxx = Specific Device Code A = Assembly Location

YY = Year WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

MAXIMUM RATINGS ($T_J = 25$ °C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	230	Vdc
Collector-Base Voltage	V _{CBO}	230	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector–Emitter Voltage – 1.5 V	V _{CEX}	230	Vdc
Collector Current – Continuous – Peak (Note 1)	I _C	15 25	Adc
Base Current – Continuous	I _B	1.5	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	P _D	200 1.43	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	- 65 to +150	°C
DC Blocking Voltage	V _R	200	V
Average Rectified Forward Current	I _{F(AV)}	1.0	A

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	0.625	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

ATTRIBUTES

Char	acteristic	Value		
ESD Protection	Human Body Model Machine Model	>8000 V > 400 V		
Flammability Rating		UL 94 V-0 @ 0.125 in		

ORDERING INFORMATION

Device	Package	Shipping		
NJL3281D TO-264		25 Units / Rail		
NJL1302D TO-264		25 Units / Rail		

^{1.} Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_C = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, I _B = 0)	V _{CEO(sus)}	230	_	Vdc		
Collector Cutoff Current (V _{CB} = 230 Vdc, I _E = 0)	I _{CBO}	-	50	μAdc		
Emitter Cutoff Current (V _{EB} = 5 Vdc, I _C = 0)	I _{EBO}	-	5	μAdc		
ON CHARACTERISTICS						
DC Current Gain	h _{FE}	60 60 60 60 60 45	175 175 175 175 175 175 -			
Collector–Emitter Saturation Voltage (I _C = 10 Adc, I _B = 1 Adc)	V _{CE(sat)}	-	3	Vdc		
DYNAMIC CHARACTERISTICS			•	1		
Current–Gain – Bandwidth Product ($I_C = 1$ Adc, $V_{CE} = 5$ Vdc, $f_{test} = 1$ MHz)	f⊤	30	_	MHz		
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	-	600	pF		
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 1.0 \text{ A}, T_J = 25^{\circ}\text{C}$) ($i_F = 1.0 \text{ A}, T_J = 150^{\circ}\text{C}$)	VF	1.0 0.83		V		
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 150^{\circ}C$)	i _R	10 100		μΑ		
Maximum Reverse Recovery Time (i _F = 1.0 A, di/dt = 50 A/μs)	t _{rr}	100		ns		

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL CHARACTERISTICS

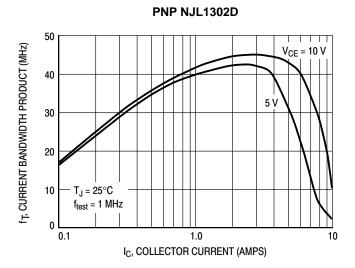


Figure 1. Typical Current Gain Bandwidth Product

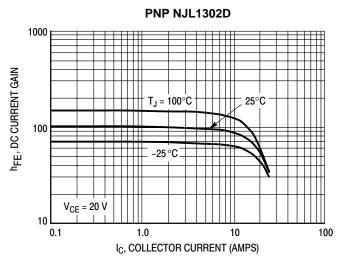


Figure 3. DC Current Gain, $V_{CE} = 20 \text{ V}$

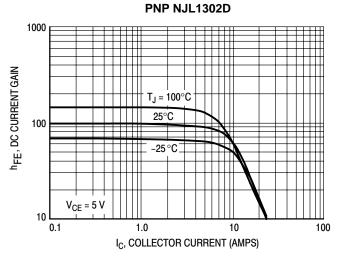


Figure 5. DC Current Gain, V_{CE} = 5 V

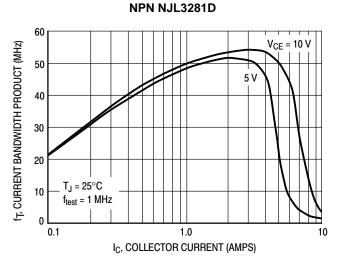


Figure 2. Typical Current Gain Bandwidth Product

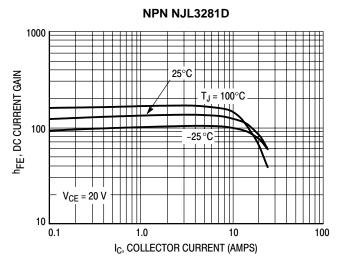


Figure 4. DC Current Gain, $V_{CE} = 20 \text{ V}$

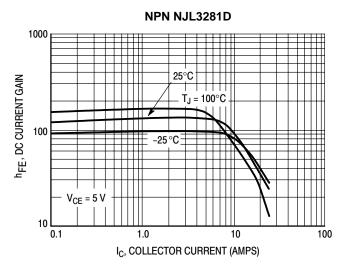
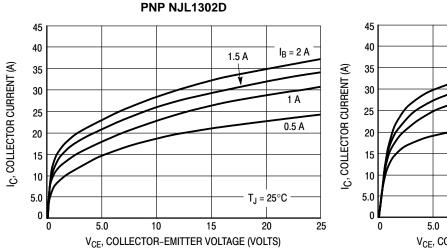


Figure 6. DC Current Gain, V_{CE} = 5 V

TYPICAL CHARACTERISTICS



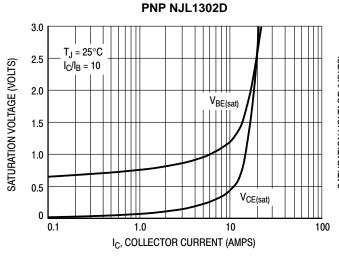
NPN NJL3281D

1.5 A | I_B = 2 A |

1.5 A |

Figure 7. Typical Output Characteristics

Figure 8. Typical Output Characteristics



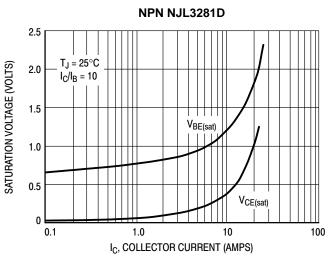
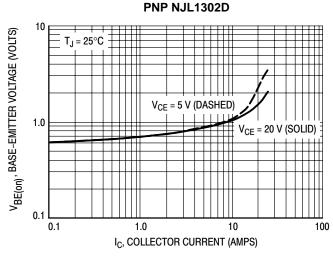


Figure 9. Typical Saturation Voltages

Figure 10. Typical Saturation Voltages



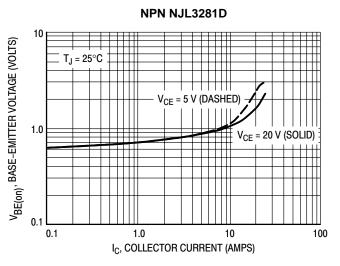


Figure 11. Typical Base-Emitter Voltage

Figure 12. Typical Base-Emitter Voltage

TYPICAL CHARACTERISTICS

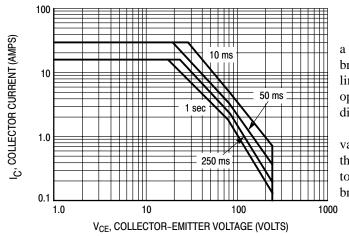


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

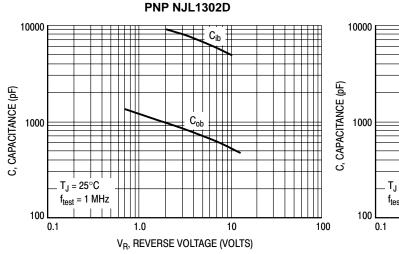


Figure 14. NJL1302D Typical Capacitance

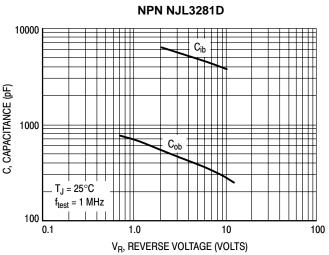


Figure 15. NJL3281D Typical Capacitance

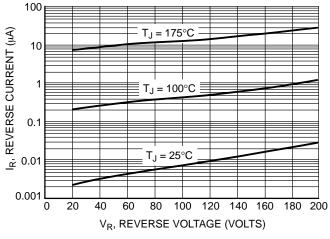


Figure 16. Typical Reverse Current

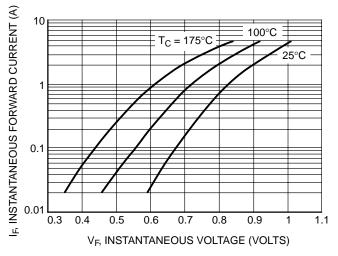
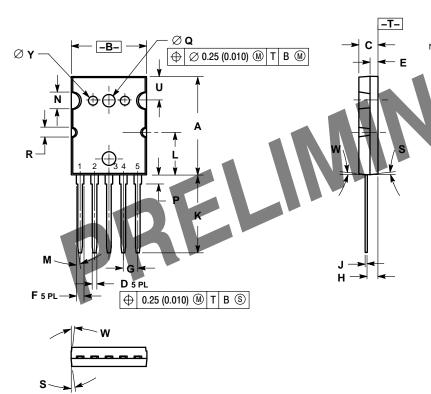


Figure 17. Typical Forward Voltage

PACKAGE DIMENSIONS

TO-264, 5 LEAD CASE 340AA-01 ISSUE O



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION; MILLIMETER.

ſ		MILLIMETERS			INCHES			
l	DIM	MIN	NOM	MAX	MIN	NOM	MAX	
	Α	25.857	25.984	26.111	1.018	1.023	1.028	
[В	19.761	19.888	20.015	0.778	0.783	0.788	
l	C	4.928	5.055	5.182	0.194	0.199	0.204	
l	D	1.	219 BS0	0	0.0480 BSC			
	Е	F 1.981 BSC			0.0800	0.0830	0.0860	
	F				0.0780 BSC			
	G				0.150 BSC			
l	Н	2.667 2.718 2.769		0.1050 0.1070 0.10		0.1090		
l	J	0.584 BSC			0.0230 BSC			
	K	20.422	0.422 20.549 20.676		0.804	0.809	0.814	
	L	11.28 REF		(0.444 REF			
	M 0 °		-	7 °	0 °		7 °	
l	N	4.57 REF			0.180 REF			
l	Р	2.259	2.386	2.513	0.0889	0.0939	0.0989	
l	Q	3.480 BSC		C).1370 B	SC		
l	R	2.54 REF		0.100 REF				
l	S	0 °		8 °	0 °		8 °	
Į	U	6.17 REF			0.243 REF			
	W	W 0 ° 6 °		0 °	-	6°		
ſ	Υ	2 388 BSC			0.0940 BSC			

- STYLE 1:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR
 4. ANODE
 5. CATHODE

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